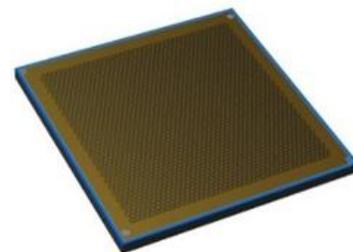


V00133

**Die; 2222; 850; M; 3B; Z10X44-4;
10W; 1.99mm x 1.99mm**



Features:

- Chip Technology: GaAs VCSEL
- Laser Wavelength: 850 nm
- Optical Power Class: 10 W
- Radiation Profile: Multi Mode
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

Ordering Information

Description	Operating Mode: $T_a = 25^\circ\text{C}; I_F = 12 \text{ A};$ $t_p = 100 \mu\text{s}; \text{DC} = 1\%$	Ordering Code
Die; 2222; 850; M; 3B; Z10X44-4; 10W; 1.99mm x 1.99mm	10 W	V00133



COMPLIES WITH IEC 60825-1, 3rd EDITION MAY 2014.

COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER

Maximum Ratings

$T_a = 25^\circ\text{C}$

Parameter	Symbol		Values
Operation/Solder temperature $t_p = 100 \mu\text{s}$; DC = 1%	T_s	min.	-40°C
		max.	110°C
Storage temperature	T_{stg}	min.	-40°C
		max.	110°C
Forward current Pulsed operation; $T_p = 100 \mu\text{s}$; DC = 1%; $T_s = 25^\circ\text{C}$	I_f	max.	20 A
Forward current Direct current operation; DC = 100%; $T_s = 25^\circ\text{C}$	I_f	max.	10 A
Reverse Voltage	Not designed for reverse operation		
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)	V_{ESD}	max.	2 kV

Note: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.

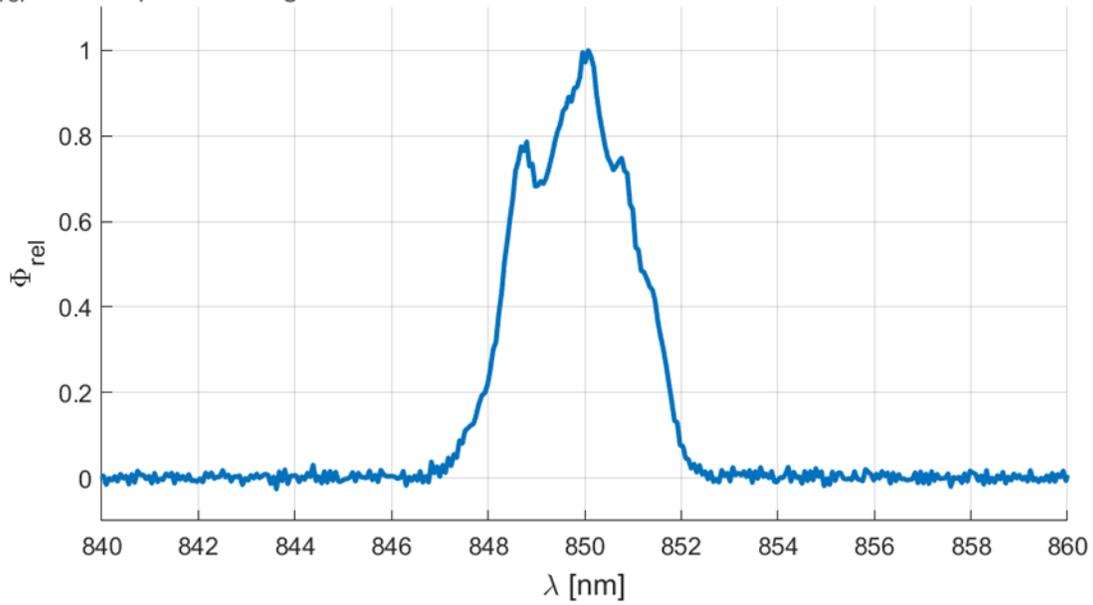
Characteristics

$T_a = 25^\circ\text{C}$, $I_F = 12\text{ A}$; $t_p = 100\ \mu\text{s}$; DC = 1%

Parameter	Symbol		Values
Forward voltage	V_F	typ.	2.1 V
Output power	Φ	typ.	10 W
Threshold current	I_{th}	typ.	2.7 A
Slope efficiency	SE	typ.	1.0 W / A
Power conversion efficiency	η	typ.	40%
Peak wavelength	λ_{peak}	min.	840 nm
		typ.	850 nm
		max.	860 nm
Spectral bandwidth at FWHM (50% of Φ_{max})	λ_{FWHM}	typ.	2 nm
Temperature coefficient of wavelength	TC_λ	typ.	0.06 nm / K
Field of view at FWHM (50% of Φ_{max})	ϕ_x	typ.	18°
	ϕ_y	typ.	18°

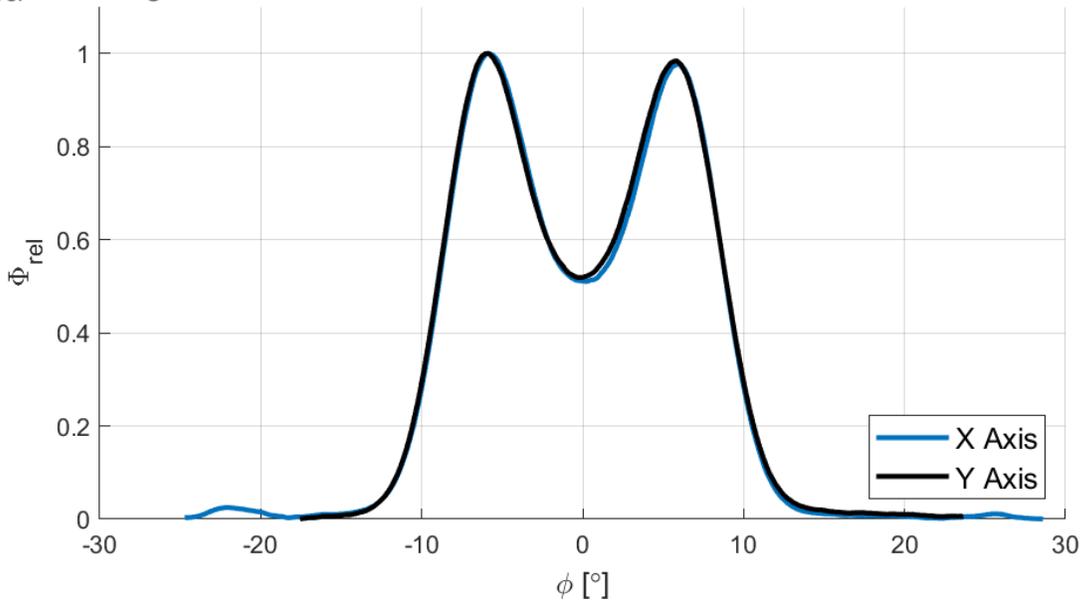
Relative Spectral Emission ¹⁾

$\Phi_{rel} = f(\lambda); I_F = 12 \text{ A}; T_S = 25 \text{ }^\circ\text{C}$



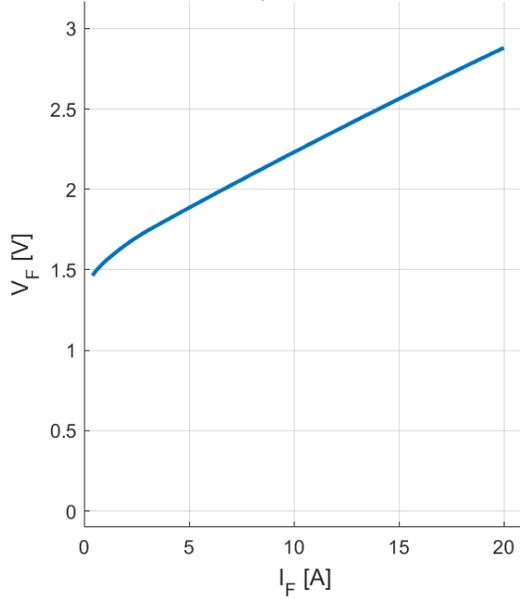
Radiation Characteristics ¹⁾

$\Phi_{rel} = f(\phi); T_S = 25 \text{ }^\circ\text{C}$



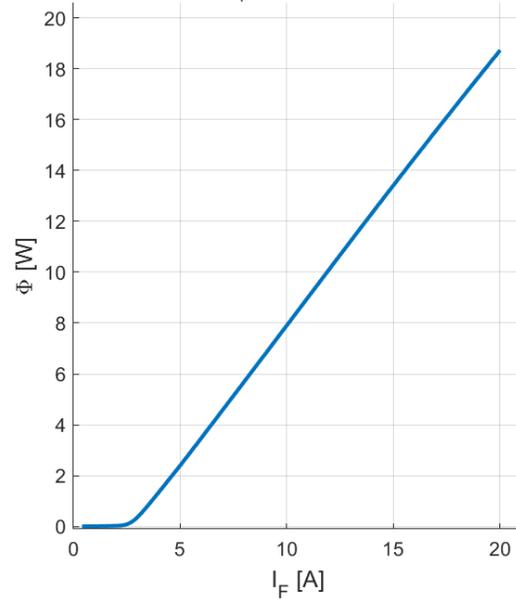
Forward Voltage ^{1) 2)}

$V_F = f(I_F); T_S = 25\text{ °C}; t_p = 100\ \mu\text{s}; \text{DC} = 1\%$



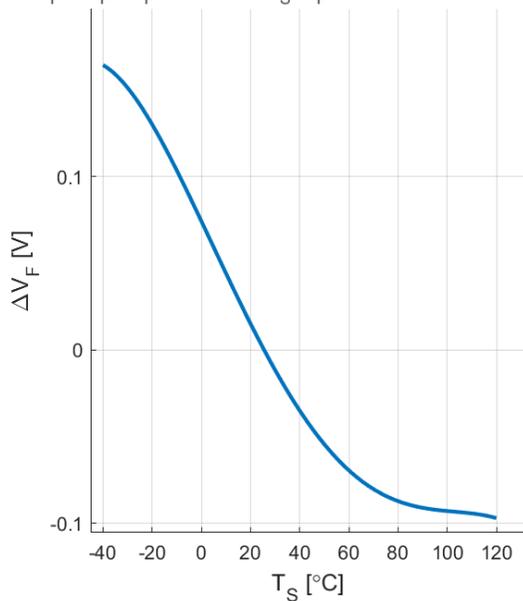
Optical Output Power ^{1) 2)}

$\Phi = f(I_F); T_S = 25\text{ °C}; t_p = 100\ \mu\text{s}; \text{DC} = 1\%$



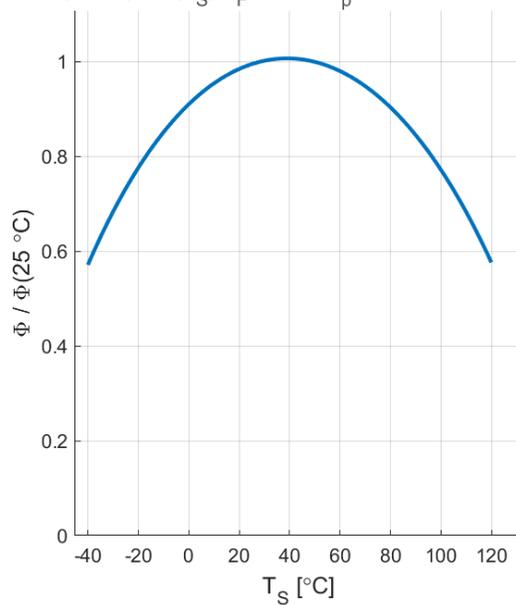
Relative Forward Voltage ¹⁾

$\Delta V_F = V_F - V_F(25\text{ °C}) = f(T_S); I_F = 12\text{ A}$



Relative Radiant Power ¹⁾

$\Phi / \Phi(25\text{ °C}) = f(T_S); I_F = 12\text{ A}; t_p = 100\ \mu\text{s}; \text{DC} = 1\%$



Product Label

VIXAR Vertical Cavity Surface Emitting Laser (VCSEL) Product

Model: _____

Manufacturer: VIXAR
2355 Polaris AVE N. SUITE 100
Plymouth, MN 55447 USA

Manufactured: Bare Die by VIXAR,
Fabricated or Packaged by: _____
City: _____, Country: _____

Wafer #: _____
Date Code: _____
Manufacturer Lot No.: _____
Quantity: _____

Complies with FDA/CDRH 21 CFR 1040.10 and 1040.11 except for deviations pursuant to Laser Notice No. 50, dated June 24, 2007.

CDRH Accession No.: 1210159-000 Product Code: RDW

Notes

Depending on the mode of operation, these devices emit highly concentrated visible and non-visible light which can be hazardous to the human eye. Products which incorporate these devices must follow the safety precautions given in IEC 60825-1.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit <http://vixarinc.com/vcSEL-technology/application-notes>

Glossary

- 1) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 2) **Testing temperature:** $T_a = 25^\circ\text{C}$
- 3) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.

Revision History

Version	Date	Change
0.0	March 19 - 2020	Initiation of preliminary datasheet
0.1	November 30 - 2020	Updated preliminary information
1.0	June 2, 2021	Release of datasheet



COMPLIES WITH IEC 60825-1, 3rd EDITION MAY 2014.

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